



## **MTP20N15EG Information**



For Reference Only

Part Number MTP20N15EG

Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 150V 20A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# **MTP20N15EG Specifications**

Manufacturer Part Number         MTP20N15EG           Manufacturer         ON Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         150V           Current - Continuous Drain (Id) @ 25°C         20A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         55.9nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1627pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         112W (Tc)           Rds On (Max) @ Id, Vgs         130 mOhm @ 10A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-220-3  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Tourent - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ### 20V  ### 250 ### #	Manufacturer Part Number	MTP20N15EG
Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         150V           Current - Continuous Drain (Id) @ 25°C         20A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         55.9nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1627pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         112W (Tc)           Rds On (Max) @ Id, Vgs         130 mOhm @ 10A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3	Manufacturer	ON Semiconductor
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Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
report errors.		Report errors?

#### **MTP20N15EG Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# **MTP20N15EG Payment Methods**



















## **MTP20N15EG Shipping Methods**













If you have any question about MTP20N15EG, please do not hesitate to contact us!

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